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Dissolution Anisotropy of Pyroxenes: Role of Edges and Corners Inferred from Stochastic Simulations of Enstatite Dissolution

3 Arnaud Bouissonnié,* Damien Daval, and Philippe Ackerer

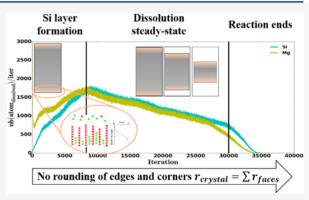


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4 ABSTRACT: Experimental studies exhibit a wide variety of dissolution s rates for a given mineral depending on the chemical conditions and also 6 on the type of experiment conducted. As a relevant example, studies 7 focused on face-specific dissolution and those focused on powder 8 dissolution can present differences of up to 1 order of magnitude. 9 Linking these two types of experiments is therefore relevant, since 10 experimental conditions can be almost entirely controlled throughout 11 the entire experiment. In this study, we use a stochastic dissolution 12 model based on hydrolysis of atomic bonds of enstatite, the magnesium 13 endmember pyroxene, to simulate the dissolution of different sizes and 14 aspect ratios of enstatite grains. This model, validated in a previous 15 study by a comparison with experimental (face-specific) rate data, is 16 used to understand the evolution of the dissolution rate with time, from



17 the beginning of the dissolution until the entire consumption of the crystal. We show that the behavior of the dissolution is controlled mainly by the aspect ratio of the grain. A simple dissolution model based on face-specific dissolution is then used to compare the results of the simulations obtained with those resulting from the grain dissolution model. The similarity between the results points out that the contribution to the dissolution of edges and corners is only modest for very anisotropic silicates such as pyroxenes, where silicate tetrahedrons are connected through chains running parallel to a given crystallographic axis. This simple model is then extended using both face-specific experimental and model results and compared to existing powder dissolution results. This comparison shows an excellent agreement between face-specific dissolution modeling and powder dissolution experiment, indicating that, for anisotropic minerals such as pyroxenes, face-specific and powder dissolution experiments can be linked, which can be of great interest for future dissolution studies.

1. INTRODUCTION

26 Dissolution kinetics is a key parameter to understand the Earth's 27 surface evolution and is crucial for several industrial and 28 environmental problems (cement dissolution, nutrient deple-29 tion in soils, etc.). Over the last decades, numerous studies have 30 helped understand the processes that occur at the mineral— 31 water interface, as well as developing different methods to 32 measure their kinetics for a wide variety of minerals. 1-9 While 33 most of these studies are based on powder dissolution 34 experiments, ^{2,10-12} fewer studies succeeded to measure 35 dissolution rates on different faces of a given miner-36 al. 3,4,6,7,9,13-16 This latter kind of studies has shown the 37 importance of the crystallographic structure (i.e., anisotropy) 38 on mineral dissolution kinetics. As a relevant example, 39 pyroxenes, which are strongly anisotropic due to their silica 40 tetrahedron chains, exhibit a strong dissolution anisotropy 41 consistent with the periodic bond chain theory. ¹⁷ However, the 42 comparison between the dissolution rates measured on single 43 faces and those measured on powder highlights a significant 44 difference (powder dissolution rates are generally higher than 45 face-specific dissolution rates 18). This adds complexity to our

ability to upscale dissolution rates and to apply experimental 46 measurements on field studies without using empirical scaling 47 parameters that complicate reactive-transport simulations. 48

As suggested by different studies, this difference may result 49 from the amount of reactive sites present in each case. 19-23 50 Indeed, considering face dissolution often means considering a 51 reactive surface which is not affected by the dissolution of 52 mineral's edges and corner. However, not only these sites are the 53 most reactive, as shown in Noiriel et al., 24,25 they are also present 54 in greater proportions in powders than on centimeter-sized 55 single crystals (if one assumes a flat surface at the beginning of 56 the experiments). Therefore, studying the contribution of these 57 corners and edges to dissolution is essential. To do so, new 58

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Kossel crystal / Calcite

Inosilicates / OrthoEnstatite



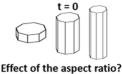






Figure 1. Schematic representation of the objectives of this paper. Dissolution is often assumed to take place on reactive sites such as edges and corners. It has been demonstrated on Kossel crystal and calcite that, during the dissolution process, the shape of the crystal evolves, and edges and corners are rounded, leading to an almost spherical shape (for Kossel crystal, depending on the activation energy of the hydrolysis) when the primal material is a cube. In this study, we aim to determine whether these considerations are applicable on inosilicates, with a specific focus on enstatite. The study is based on simulations using a stochastic dissolution model applied at the atomic bond level and aims to explore different aspect ratios of the initial mineral parallelepipedal shape.

59 experimental setups have emerged, using analytical techniques 60 such as X-ray tomography^{24–26} or vertical scanning interferom-61 etry.²⁷ However, despite their increasing efficiency to study the 62 processes that occur at finer scales (micrometer to nanometer 63 scale), they often need to be combined with numerical studies to 64 unravel what happens at the solid—fluid interface.

Numerical experiments have become a powerful tool to 66 improve our understanding of processes occurring at the water— 67 mineral interface, ranging from molecular dynamics to reactive- 68 transport model used at pore scale. $^{28-30}$ The last decades have 69 also seen the development of stochastic dissolution models, such 70 as kinetics Monte Carlo models or Voronoi method. 13,19,23,31-38 These models, based on a relation between the activation 72 energies of individual processes (bond hydrolysis, for example) 73 and their occurrence probability, allow for fast computation and 74 the simulation of larger objects, which classical molecular dynamics is not able to deal with. These models, first applied on 76 Kossel crystals, have brought or validated many important results. As an example, numerous studies applied on Kossel crystals validate the difference of reactivity between the crystal's 79 edges, corners, and surfaces. 19 The work of Zhang and Luttge 35 80 also mentioned these differences for feldspar dissolution. 81 However, providing a generalization to other minerals, which 82 is an intrinsic issue belonging to the field of physical chemistry, is 83 important and may present a great interest to link laboratory and 84 field observations, as mentioned by Noiriel et al. 25

For several reasons, pyroxenes represent a relevant target to 86 address these aspects. Indeed, not only do they have a strongly anisotropic structure (silica chains running parallel to a given crystallographic axis), but they are also present worldwide and 89 represent a major group of minerals for reactive-transport 90 models. ^{39,40} In two previous studies, ^{16,41} we described a 91 stochastic dissolution model operating at atomic scale and 92 applied to enstatite, the magnesian endmember of pyroxenes. This model, validated by a comparison between simulations and 94 experimental results, has shown its ability to reproduce the dissolution anisotropy of enstatite as well as the surface features 96 observed at the end of the experiments (etch pit morphology, and relative thickness of the silica layers developed on each face). 16 However, in these two studies, we focused on face-99 specific dissolution, neglecting the contribution of "macro-100 corners" and "macro-edges", which can represent, for some 101 minerals such as calcite, the most reactive sites. 25 In the present 102 study, we propose to simulate the dissolution of enstatite 103 rectangular parallelepipeds. Different sizes and aspect ratios are

modeled and analyzed, to understand if the dissolution of 104 enstatite grains can be described mathematically using 105 parameters related to the grain dimensions, as well as to 106 understand if observations made on calcite^{2.5} are expandable to 107 enstatite, and more generally, to pyroxenes. Another objective 108 deals with the impact of the aspect ratio of a grain on the 109 dissolution rate. Powder experiments present a wide variety of 110 grain morphologies resulting from the crushing of macro- 111 crystals. These different shapes and sizes may affect the 112 dissolution rate, since the dissolution rate is face-specific. 3,15,16 113 Furthermore, different grain sizes may imply a greater rate 114 variability through the development of fast dissolving micro- 115 facets at mineral's edges and corners. These questions are 116 summarized in Figure 1.

2. METHODS

2.1. Model Description. A complete description of the 118 model is given in Bouissonnié et al. 16 Briefly, atoms contained in 119 the enstatite cell are placed using Pbca space group symmetry 120 elements, using the cell parameters (a = 18.233 Å, b = 8.8191 Å, 121 and c = 5.1802 Å) and the coordinates given by Hugh-Jones and 122 Angel.⁴² Each magnesium and silicon atom is linked to oxygen 123 according to their coordination. However, the dissolution of 124 oxygen atoms is never considered in the dissolution model. 125 Indeed, they are considered as bridging atoms 13 and the 126 dissolution model is applied on M-O_{br}-M bonds (M being a 127 Mg or Si atom). All atoms linked to another one via a bridging 128 oxygen are part of its first coordination sphere. 13 Only the first 129 coordination sphere is taken into account to compute the bond- 130 breaking probabilities, since previous results showed that this 131 strategy results in a satisfactory agreement between modeled and 132 experimental results.16

Usually, the probability attributed with one event (i.e., the 134 bond-breaking probability) is written as follows³⁸

$$P = e^{-E_a/k_BT} (1)_{136}$$

where P stands for the bond-breaking probability, $E_{\rm a}$ is the 137 activation energy of the bond hydrolysis (J), $k_{\rm B}$ is the Boltzmann 138 constant (J/K), and T is the temperature (K). In the present 139 study, the greatest bond-breaking probability (i.e., the bond 140 hydrolysis associated with the lowest activation energy, Mg-O-141 Mg) was arbitrarily set to 0.99 and the two other probabilities 142 were scaled according to the differences between their 143 corresponding activation energies following

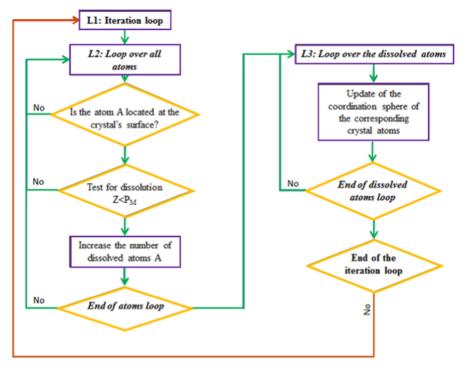


Figure 2. Scheme of the dissolution algorithm used in the dissolution model. This scheme is adapted from Bouissonnié et al.⁴¹

$$\frac{P_{\rm A}}{P_{\rm B}} = e^{-(E_{\rm a}^{\rm A} - E_{\rm a}^{\rm B})/k_{\rm B}T} \tag{2}$$

146 where A and B represent two different bonds. According to the 147 best agreement between modeled and experimental results 148 developed in Bouissonnié et al., ¹⁶ the other two probabilities 149 were calculated as 0.4 and 0.0146 for Mg–O–Si and Si–O–Si, 150 respectively. The probability of backward reactions (i.e., the 151 creation of a new bond, previously destroyed or not) is not 152 considered here since the model is applied to reproduce 153 experiments run at pH 0, ¹⁶ where these reactions can be 154 neglected.

As it has been shown to successfully reproduce experimental data and observations, an "all-or-none" approach was used in this study. 13,19,35–37,43,44 This approach considers that an atom series is released only if all bonds that connect it to the surface are simultaneously broken during a single iteration step. Hence, the numerical model works directly on the atoms, and not on the bonds. Then, the overall probability of an atom to be released into solution during one iteration is given by the product of all of the probabilities corresponding to the different bonds it shares with other atoms

$$P_{\rm M} = e^{-nE_{\rm M-O-Mg}/k_{\rm B}T}e^{-mE_{\rm M-O-Si}/k_{\rm B}T} = P_{\rm M-O-Mg}^{n}P_{\rm M-O-Si}^{m}$$
165 (3)

166 where n and m stand for the number of bonds that the 167 considered atom shares with neighboring Mg and Si atoms, 168 respectively.

2.2. Dissolution Algorithm. At each iteration step, all 170 atoms located at the surface are scanned. An atom is considered 171 at the surface if its first coordination sphere is incomplete. A 172 random number Z is generated for each atom; if $Z < P_M$, the 173 atom is released into the solution, if not, the scan of the atoms 174 moves on. At the end of the iteration, i.e., after scanning all atoms 175 located at the surface, the attributes of the atoms contained in 176 the first coordination sphere of those which have been dissolved

during the iteration, are updated to consider this change, 177 resulting in an increase of their departure probability at the next 178 iteration. It is essential to update the attributes of the considered 179 atoms only at the end of an iteration to avoid an "in cascade" 180 dissolution, where the atoms would be released one after the 181 other due to a direct change of the probabilities. A scheme of the 182 algorithm is shown in Figure 2.

2.3. Output of the Model. The dissolution was monitored 184 based on the release of Si atoms, as in classical studies dedicated 185 to silicate dissolution kinetics. Note that because the dissolution 186 at steady state (i.e., the dissolution rate can be considered to be 187 constant) is stoichiometric, ¹⁶ this choice has no consequence on 188 what will be described in the present study. However, the 189 behavior of Mg release is important at the beginning of the 190 dissolution process ¹⁶ and will be discussed in the section 191 corresponding to this part of the dissolution timeline.

In the literature, the term "mineral dissolution rate" is usually 193 used to refer to the release rate of atoms in the solution from a 194 mineral surface, whether or not it is normalized to the contact 195 surface between the fluid and the mineral. To avoid any 196 confusion, in the following, we will use the term "dissolution 197 rate" to refer to a velocity that is not normalized to the surface 198 area (unit: mol/iteration) and "dissolution flux" to refer to 199 dissolution rates normalized with respect to the surface area 200 (unit: mol/m²/iteration). Both quantities are calculated at each 201 iteration for any numerical simulation.

The cumulated number of released atoms has been used to 203 calculate the total surface retreat during the simulations 204 corresponding to the dissolution of single faces (i.e., only one 205 face is considered to be in contact with the solution). The 206 surface retreat is defined as the average height of material lost 207 during the dissolution. It is calculated as follows

$$\Delta h_i^{(hkl)} = \frac{a^*b^*c}{16^*S_f} \sum_{i}^{n=1} nb(Si_{d,n})$$
(4) ₂₀₉

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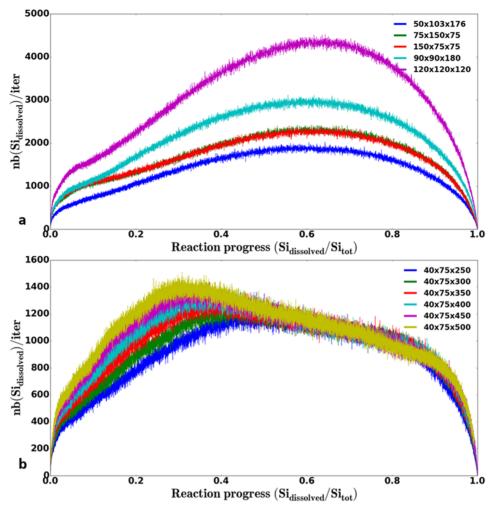


Figure 3. Results of the dissolution model showing the dissolution rate (defined as the number of Si atoms released per iteration) as a function of the reaction progress. Legends indicate how many times the crystal cell is multiplied in x, y, and z directions. The results reported here represent sets of simulations applied on arbitrary parallelepiped sizes (i.e., not representative of the aspect ratio of natural enstatite). (a) First subgroup of simulations, with arbitrary rectangular parallelepiped dimensions. (b) Second subgroup: Length and width (parallel to the a and b axes of the enstatite cell) of the rectangular parallelepiped were kept constant while the height (parallel to the c axis) was modified in the different simulations. In both cases, a similar behavior is observed. (a) Simulations highlight a parabolic behavior of the dissolution. The maximum seems to be observed at similar values of the reaction progress. (b) Contrary to the first set, the simulations of the second set are different at the beginning of the dissolution. Here, the larger the crystal, the higher the maximum. After reaching the maximum, the number of Si atoms dissolved decreases linearly. The slope is the same for each simulation.

where $\Delta h_i^{(hkl)}$ is the surface retreat at the *i*th iteration (m); *a, b,* 211 and *c* are the cell parameters (m); S_f is the surface area of the face 212 (m²); and $nb(Si_{d,i})$ is the number of Si atoms dissolved at the *i*th 213 iteration. The number 16 corresponds to the number of Si atoms 214 in the enstatite cell. This method has been validated in 215 Bouissonnié et al. ¹⁶ and gives identical results to those obtained 216 if the mean coordinates in the direction normal to the surface 217 were used.

Finally, the last parameter used in this study is the advancement of the dissolution reaction. It is defined as the ratio between the number of Si atoms dissolved from the beginning of the simulation and the initial number of Si atoms at the beginning of the simulation.

223 **2.4.** Assumptions and Limitations of the Model. The 224 model has proven its ability to reproduce both experimental 225 dissolution rates and observed surface features evolutions. 226 However, several assumptions (all based on the studied 227 chemical condition) are considered and may impact the 228 model outputs and their upscaling to study natural environment:

- No backward reactions (i.e., formation of atomic bonds) 229
 are implemented. This simplification was made because of 230
 the very low pH of the studied solution (pH 0). This pH 231
 makes the solution to be very far from the thermodynamic 232
 equilibrium with respect to enstatite. Therefore, backward 233
 reactions (i.e., formation of atomic bonds) are considered 234
 unlikely to happen. 235
- The dissolution algorithm is applied on atoms rather than 236 atomic bonds. This method is commonly used in 237 stochastic dissolution studies, however, combined with 238 the first assumption, this precludes the formation of 239 amorphous silica layers resulting from interfacial dis-240 solution—reprecipitation 45 or reorganization of dangling 241 bonds. In the present study, such layers are suspected to 242 have no impact on the dissolution rate because their 243 passivating ability is thought to be pH-dependent 14,47 and 244 passivating layers are unlikely to form in strongly acidic 245 environments. Such conditions may limit the extension of 246 the conclusions of the study to less acidic environments. 247

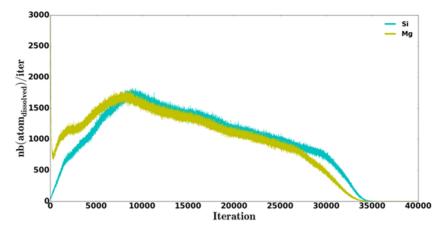


Figure 4. Example of the results of a simulation conducted on a $40a \times 82b \times 700c$ volume. This figure shows the dissolution rate (number of dissolved atoms per iteration) as a function of the number of iteration steps. The cyan curve represents Si atoms, and the dark yellow curve represents Mg atoms. Contrary to the Si curve, which increases continuously at the beginning of the simulation, the Mg curve is marked by a sharp decrease of the number of atoms released per iteration. This is explained by the fast depletion of superficial Mg, which have a high probability of departure. After reaching the maximum value of the amount of Si and Mg released per iteration (corresponding to the iteration where the silica layer reaches a constant thickness), the dissolution rate decreases continuously and the dissolution is stoichiometric.

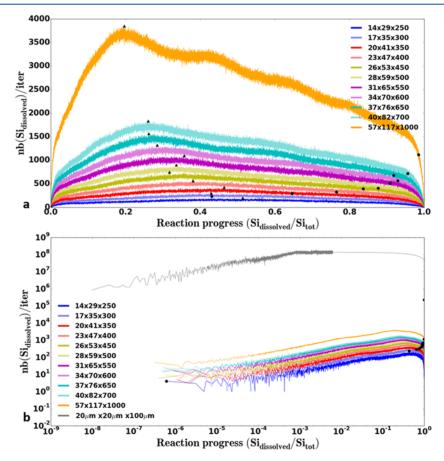


Figure 5. (a, b) Results of the dissolution model showing the dissolution rate (defined as the number of Si atoms released per iteration) as a function of the reaction progress. Legends indicate how many times the crystal cell is multiplied in x, y, and z directions or exact dimension (black line). Each panel represents Si dissolution rate as a function of the reaction progress for the set of simulations that observe realistic aspect ratios for the grains, plotted in standard and logarithmic scales, respectively. Black triangles indicate the reaction progress where the dissolution rate reaches its maximum. Black circles indicate the reaction progress where the volume of the enstatite grain is equivalent to that of the initial smallest simulated rectangular parallelepiped ($14 \times 29 \times 250$). For each simulation, the dissolution rate increases at the beginning of the process, until reaching Aconitum maximum value. After the maximum value is reached, the dissolution rate decreases linearly until the reaction progress reaches \sim 95%. The duration of the linear decreasing phase depends on the crystal size: the larger the crystal, the longer the linear phase.

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- would be unstable and therefore, would not be ratecontrolling of the dissolution process.⁴⁸
 - The simulations correspond to conditions where the aqueous solution is continuously stirred, resulting in no local variations of the saturation index of the solution. Therefore, the saturation index is supposed to be constant (and far from equilibrium), both in space and time.

3. RESULTS

2.54

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3.1. Evolution of Si Dissolution. A total of 22 different enstatite volumes have been simulated. In the following, each volume is named after the number of cells in the three spatial directions.

The first 11 simulations were conducted using arbitrary volumes to highlight potential similarities between their dissolution behaviors. The results of these simulations are given in Figure 3. This group of simulations can be separated into two main subgroups (Figure 3a,b). The first subgroup (Figure 3a) presents results of simulation runs with initial aspect ratios that have no particular relation to each other, unlike the results of simulations simulations made (Figure 3b), which contains simulations made on grains varying only in height (the length in the x and y directions having been kept constant).

The first subgroup is marked by a sharp increase of the 273 274 amount of dissolved Si atoms within the first 3-5% of the 275 reaction, which corresponds to an increase from 0 to 500-1400 276 Si atoms released into solution per iteration, depending on the 277 initial volume. After this first step, the behavior of the release rate 278 of Si differs from the simulated volume. Indeed, while smaller 279 volumes $(50 \times 103 \times 176, 75 \times 150 \times 75 \text{ and } 150 \times 75 \times 75)$ are 280 characterized by a linear increase extending over almost 40% of 281 the reaction, the others $(90 \times 90 \times 180 \text{ and } 120 \times 120 \times 120)$ 282 show a shorter linear evolution (only 20% of the total reaction). 283 In each case, after the linear increase of the release rate of Si into 284 solution, a slower increase is observed until the dissolution rate 285 reaches its maximum, which occurs after a similar reaction 286 progress (between 60 and 65%) for all volumes of this subgroup. 287 The dissolution rate reaches ~1900, 2300, 2300, 2950, and 4350 Si atoms/iteration for the $50 \times 103 \times 176$, $75 \times 150 \times 75$, 150×75 289 75 \times 75, 90 \times 90 \times 180, and 120 \times 120 \times 120 volumes, 290 respectively. After this maximum is reached, the dissolution rate 291 of Si decreases until the reaction is complete, and all of the crystal has been dissolved. This step extends over the last 35-40% of the total reaction.

The second subgroup of simulations is composed of six 295 different volumes. While these volumes differ in height (length 296 in the z direction parallel to the c axis), the lengths in the x and y directions were kept constant. Hence, the surface area of (100) and (010) faces varied, unlike that of the (001) faces. The onset 299 of the simulations exhibits a similar behavior to that described 300 for the first subgroup: the first 3% of the reaction is characterized by a sharp increase (from 0 to 350-600 Si atoms/iteration) of 302 the release rate of Si. This step is followed by a linear increase of the dissolution rate until it reaches its maximum. Contrary to the 304 first subgroup of simulations, the advancement corresponding to 305 this maximum depends on the size of the initial volume. Indeed, 306 if the maximal dissolution rate is greater for the largest volume 307 (1390 Si atoms/iteration for the volume $40 \times 75 \times 500$) 308 compared to the smallest one (1190 Si atoms/iteration for the 309 volume 40 \times 75 \times 250), the advancement at which the 310 maximum is reached is lower (0.30 against 0.45, respectively). 311 Another difference between the first and second subgroups is the

behavior of the dissolution after the maximum is reached. While, 312 in the first case, the dissolution rate decreases sharply until the 313 end of the reaction, in the second case, a slow and linear decrease 314 is observed from an advancement of 30–45 to 85–90% 315 depending on the considered volume. During this linear 316 decrease, regardless of the volume, all simulation results are 317 almost identical, showing the same dissolution rate of Si atoms at 318 the same advancement of reaction. The last 10–15% of the 319 reaction is characterized by a sharp decrease of the dissolution 320 rate of Si atoms to finally reach 0 when the reaction is complete 321 (Figure 4).

The second group of eleven simulations is shown in Figure 5. 323 fs Contrary to the previous group of simulations, the aspect ratios 324 which were used are representative of natural enstatite crystal 325 habit. In spite of these differences, the evolution of the 326 dissolution rate of Si atoms is almost identical to that described 327 for the second subgroup of the first group described above, with 328 the following steps: (1) a sharp increase of the Si dissolution rate 329 during the first 3% of the dissolution, (2) a linear increase until 330 the maximum is reached (from 145 to 3660 Si atoms released 331 per iteration, reached after a reaction progress of 40-20% for the 332 smallest and the largest volumes, respectively), (3) a linear 333 decrease in the release rate of Si until 90-95% of the reaction, 334 and finally (4) a sharp decrease in the release rate of Si over the 335 last 5-10% of the reaction.

3.2. Evolution of Mg Dissolution. The behavior of Mg 337 dissolution is similar to the one described above for Si 338 dissolution (Figure 4). The main differences are observed at 339 the very beginning and at the end of the simulations. Mg 340 dissolution evolution has been studied only for simulated 341 volumes representative of natural aspect ratios of enstatite. 342 Because all simulations, as for Si atoms, exhibit a similar 343 behavior, only one case is shown in Figure 4 ($^{40} \times 82 \times 700$). 344 The global trend of Mg dissolution evolution is as follows:

- A dramatic decrease of the dissolution rate at the 346 beginning of the reaction (325 iterations for the volume 347 shown in Figure 4).
- An increase of the dissolution rate from the 315th to the 349 8000th iterations. This increase is marked by two pulses 350 for the volume presented in Figure 4.
- A linear, slow decrease of the dissolution rate, similar to 352 the one observed in the case of Si dissolution. In the 40 × 353 82 × 700 volume, this step extends from the 8000th to the 354 26 990th iterations.
- A more pronounced decrease in the dissolution rate for 356 the last iterations until all of the Mg atoms have been 357 dissolved.

3.3. Dissolution Normalized Per Surface Unit. Because 359 the most realistic cases treated in this study are those that 360 observe the aspect ratio of pyroxenes, only the corresponding 361 simulations were investigated with respect to a normalization 362 per surface unit. The evolution of the surface area is not derived 363 from direct outputs of the simulations. Instead, it is assumed that 364 the surface decreases according to the retreat of each single face 365 of the simulated volumes. In Bouissonnié et al., ¹⁶ we investigated 366 the surface retreat of (100), (010), and (001) faces, 367 demonstrating that our model was able to reproduce observed 368 experimental data. Similar simulations were then used to 369 calculate the evolution of the surface area of the simulated 370 crystals according to the following equation

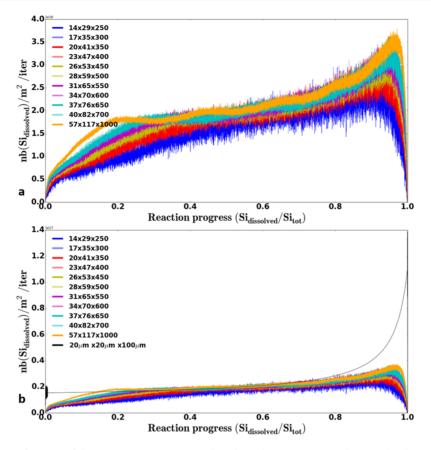


Figure 6. Dissolution flux as a function of the reaction progress. Legends indicate how many times the crystal cell is multiplied in the *x*, *y*, and *z* directions. (a) Results of the simulations. (b) Results of the simulations and modeled theoretical result for enstatite grain with realistic grain size (black curve). The black patch at the beginning of the realistic grain size dissolution corresponds to the stages 1 and 2 of **Figure 9a,b**. In each case, the dissolution flux increases at the beginning of the simulations. After reaching a given value of the reaction progress (corresponding to the 8000th iteration), the increase slows down and the dissolution flux can be considered as constant for few iterations (the larger the crystal, the longer the "steady-state" regime). Then, a moderate increase is observed until the dissolution reaches its maximum. After reaching its maximum, the dissolution flux decreases dramatically and reaches zero when all of the atoms have been dissolved.

$$A(i) = 2[(x_0 - 2\Delta h_i^{(100)})(y_0 - 2\Delta h_i^{(010)}) + (y_0 - 2\Delta h_i^{(010)})(z_0 - 2\Delta h_i^{(001)}) + (x_0 - 2\Delta h_i^{(100)})(z_0 - 2\Delta h_i^{(001)})]$$
(5)

where A(i) is the surface area at the ith iteration; x_0 , y_0 , and z_0 are the initial lengths in the x, y, and z directions, respectively; and 50 $\Delta h_i^{(hkl)}$ is the surface retreat of the corresponding (hkl) face at the ith iteration, derived from the simulations performed on single faces where the edges were constrained to be nonreactive. This method, however, does not take into account a possible rounding of the edges, often observed in mineral dissolution experiments and modeling. The number of Si atoms released at each iteration is then divided by the surface area at the corresponding iteration.

Results are shown in Figure 6. The trends followed by the dissolution fluxes differ from those obtained for dissolution sets rates. The first 3.5-1% of reaction is characterized by a sharp necessary increase in the dissolution flux from 0 to $5.4-6.2 \times 10^{15}$ Si atoms/(m² iteration) for the smallest and largest volumes, see respectively. The increase in the dissolution flux is then less pronounced over the next 42.5-19% of the reaction. The Si dissolution flux reaches 1.6×10^{16} Si atoms/(m² iteration) at 47% of the reaction progress for the smallest volume against 1.8×10^{16} Si atoms/(m² iteration) at 20% for the largest one. After

this period, the dissolution flux tends to stabilize for the three 393 largest volumes but only over a short reaction progress 394 (approximately 10% of the total reaction). After this phase, 395 the dissolution flux of the largest volumes follows that of the 396 smallest ones. The dissolution flux still increases, but the 397 difference between each iteration is less pronounced until the 398 reaction progress reaches 90-96% (where the dissolution flux 399 reaches its maximum: $(2.2-3.5)\times 10^{16}$ Si atoms/(m² iteration) 400 for the smallest and largest volumes, respectively). Finally, from 401 90 to 96% of the dissolution, the Si dissolution flux decreases 402 sharply to reach 0 when the volume has been completely 403 consumed.

4. DISCUSSION

4.1. Evolution of Mg and Si Dissolution Rates. 405 *4.1.1. Evolution during the First 8000 Iterations.* Despite the 406 differences in volumes used in the simulations, all simulation 407 outputs are characterized by a sharp increase of the number of Si 408 atoms released at the beginning of the dissolution. Figures 3a 409 and 5b show this increase as a function of the advancement of 410 the dissolution reaction. Depending on the volumes, the 411 advancements corresponding to this stage are different. 412 However, a clear pattern is highlighted when this evolution is 413 considered as a function of the number of iteration steps (i.e., 414 time) (Figure 7a). The dissolution rate is always at maximum 415 f7 around the same iteration (≈8000th) for the different volumes. 416

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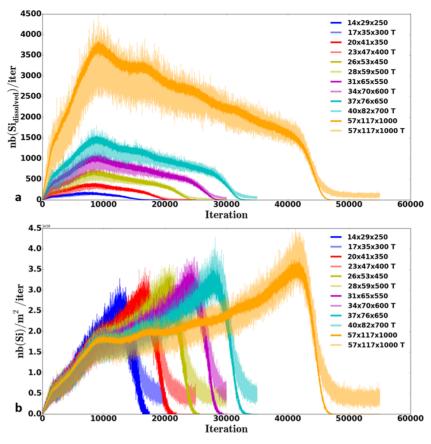


Figure 7. (a) Dissolution rate as a function of the total number of iteration steps (equivalent to time). Legends indicate how many times the crystal cell is multiplied in the *x*, *y*, and *z* directions. Light-colored curves represent the evolution of the number of Si atoms released per iteration based on theoretical considerations developed in Section 4.2. Dark-colored curves represent the simulation results of the stochastic dissolution of rectangular parallelepipeds. (b) Dissolution flux as a function of the total number of iteration steps. Light-colored curves represent the evolution of the number of Si released per iteration and per surface unit based on theoretical considerations developed in Section 4.2. Dark-colored curves represent the simulation results of the stochastic dissolution of rectangular parallelepipeds. In each panel, the agreement between theory and simulation outputs highlights the slight effects of edges and corners on the global rate/flux. The difference between theory and simulation outputs at the end of the simulations is due to the assumptions underpinning the theoretical model (see text for details).

417 Interestingly, this value corresponds to the one where the surface 418 retreat of the (001) face reaches the steady state when the set of 419 probabilities used is [0.99, 0.4, 0.0146] for [Mg-O-Mg, Si-420 O-Mg, Si-O-Si] bonds respectively. 16 It was interpreted as 421 the moment when the dissolution becomes congruent. Considering that the other faces reach their steady-state dissolution regime before the (001) face, 16 the fact that the dissolution rate of the simulated rectangular parallelepipeds is at maximum at the iteration corresponding to the attainment of a 425 426 steady state for face (001) may mean that the evolution of the dissolution regime of a simulated rectangular parallelepiped 42.7 enstatite is controlled by the face for which this steady state is reached the latest (after the largest number of iterations). Alternatively, another explanation could be that the face (001) being the fastest to dissolve, the amount of Si released from this face is greater than those of the other faces. Hence, this relation between a simulated rectangular parallelepiped enstatite and the (001) face reaching their steady state at the same iteration may come from the fact that a significant proportion of their dissolution is supported by the (001) face.

Regarding the dissolution rate of Mg atoms, Figure 4 shows that it decreases dramatically during the first few hundred iterations (325 for the volume $40 \times 82 \times 700$). This can be explained by the fast departure of Mg atoms from the reactive surface at the beginning of the simulations because of their

greater probability to be dissolved. This results in a fast leaching 442 step at the beginning of the reaction, when these atoms are 443 numerous. After a few iterations, the main coordination of Mg at 444 the surface increases prior reaching a constant value, 41 making 445 them more difficult to dissolve.

The fast decrease of Mg dissolution rate can also be linked to 447 the increase of Si dissolution rate. Indeed, the fewer the Mg—O— 448 Si bonds, the higher the Si departure probability. In other words, 449 when numerous Mg atoms are released into solution, the 450 dissolution of Si atoms is enhanced. This departure of Si atoms 451 resulting from the fast leaching of Mg atoms at the surface also 452 makes it easier for the "solution" to reach the Mg atoms located 453 deeper in the simulated crystals. These combined effects 454 possibly explain why, after a dramatic decrease, the Mg 455 dissolution rate increases with Si dissolution, until the maximum 456 is reached. After the maximum is reached, both Si and Mg 457 dissolution rates decrease. More importantly, these decreases 458 are almost identical (same slope), indicating that the dissolution 459 is stoichiometric.

4.1.2. Parameters Controlling the Dissolution. Although the 461 first set of simulated rectangular parallelepipeds was not 462 representative of the aspect ratio of natural enstatite grains, 50 463 it allows highlighting some behaviors and parameters that may 464 control the dissolution. Indeed, the two subgroups presented in 465 Figure 3 have their own patterns that can help understand the 466

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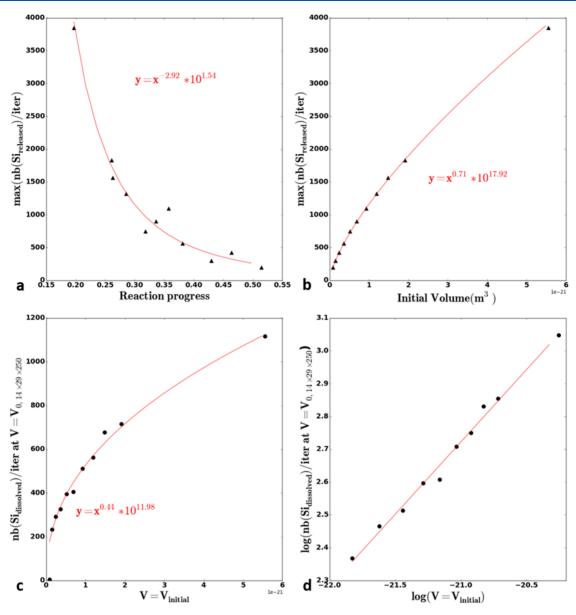


Figure 8. (a) Maximum dissolution rate as a function of the progress of the dissolution process for various initial volumes. Each triangle represents a different initial volume. The maximal value corresponds to the largest volume and the minimal to the smallest. (b) Maximum dissolution rate as a function of the initial volume. (c, d) Dissolution rate when the volume of the enstatite grain reaches the initial volume of the smallest simulated rectangular parallelepiped $(14 \times 29 \times 250)$ as a function of the initial simulated enstatite rectangular parallelepiped volume represented in standard and logarithmic scales, respectively.

ı

 $_{467}$ two principal factors impacting the dissolution, namely, the length of the rectangular parallelepiped in the z-direction and $_{469}$ the surface area of the (001) face. The most striking feature is the varying one of the subgroup composed of rectangular parallelepipeds varying only by their heights ($40 \times 75 \times 250$, $40 \times 75 \times 300$, $40 \times 75 \times 350$, $40 \times 75 \times 400$, $40 \times 75 \times 450$, and $40 \times 75 \times 500$). While the beginning of the dissolution differs depending on the volume, the stage depicting a decreasing reactivity is characterized by a similar trend and value of Si dissolution rates for all simulations (Figure 3b). Therefore, it can be assumed that this stage is controlled mostly by the surface area of the (001) faces. Then, the surface area of the (100) and (010) faces would only affect the reaction progress required to reach this stage (the greater these surfaces, the longer the preliminary tage).

This assumption can be verified with the second subgroup of 482 simulated rectangular parallelepipeds ($50 \times 103 \times 176, 75 \times 150$ 483 \times 75, 150 \times 75 \times 75, 90 \times 90 \times 180, and 120 \times 120 \times 120). 484 Indeed, the only simulations presenting the same (001) surface 485 area are those conducted with the $75 \times 150 \times 75$ and $150 \times 75 \times 486$ 75 volumes. These two rectangular parallelepipeds have the 487 same dissolution behavior throughout the entire reaction 488 (Figure 3a). While this similarity supports that the dissolution 489 is primarily controlled by the face (001), it also suggests that the 490 other two faces have only a minor contribution to the overall 491 dissolution rate of enstatite grains. This is further supported by 492 the differences in reaction rates between the three faces ((100), 493 (010), and (001)). The dissolution rate of the (001) face is more 494 than 1 order of magnitude higher than those of faces (100) and 495 (010). To have a significant impact on the total dissolution rates, 496 the surface area of the (100) and (010) faces should be at least 497

498 10 times greater than that of the (001) face, which was never 499 investigated in this study due to computational capacities and 500 our commitment to perform simulations that observe as much as 501 possible the aspect ratios of enstatite grains encountered in 502 natural environments.

The difference in shape between the released Si curves of the 504 two subgroups (Figure 3a vs Figure 3b) is more difficult to 505 explain. The main difference in the simulation parameters 506 resides in the dimensions of the simulated volumes and mainly, 507 their heights. Indeed, the heights (length in the z direction) of 508 the subgroup composed of the $50 \times 103 \times 176$, $75 \times 150 \times 75$, 509 $150 \times 75 \times 75$, $90 \times 90 \times 180$, and $120 \times 120 \times 120$ rectangular 510 parallelepipeds are smaller than those of the volumes of the second subgroup. It is therefore possible that the former 512 volumes are consumed before reaching a stage where the Si 513 dissolution rate decreases linearly, which would explain this 514 difference in behavior. If the overall dissolution is mainly 515 controlled by the dissolution of the (001) faces, it is indeed 516 possible that these volumes cannot reach this dissolution stage 517 because their height is too short. This is consistent with the 518 evolution of the dissolution rate of the other subgroup for which 519 the smaller the volume, the shorter the linear stage. It can be 520 reasonably assumed that rectangular parallelepipeds with a very 521 short height never reach a stage where the dissolution rate decreases linearly.

To conclude, the simulations shown in Figure 3 provide s24 important information regarding the global dissolution of a s25 rectangular parallelepiped enstatite: the dissolution rate seems s26 mainly controlled by that of the (001) faces.

The simulations conducted with the second set of rectangular parallelepipeds, more representative of the natural crystal habit parallelepipeds, also exhibit specific patterns. Indeed, while the same amount of Si atoms released at each iteration varies from one volume to another, trends and shapes are identical (Figure 5). This could indicate that the overall evolution of the dissolution is directly controlled by the shape of an enstatite grain. For the same aspect ratio, the initial volume only influences the absolute amount of released atoms.

This simulation set allows focusing on a quantity that delineates a transition in the evolution of the dissolution rate of a rectangular parallelepiped enstatite, namely, the maximum value this latter can reach (black triangles in Figure 5a). While it obvious that the bigger the volume of a rectangular parallelepiped, the greater the instantaneous Si dissolution rate, interestingly, it is possible to link these two quantities mathematically (Figure 8b). In the same way, it is possible to the link this maximum rate to the reaction progress (Figure 8a). The same corresponding relations are given by

$$\max(\text{Si}_{\text{released}}) = 10^{17.9} \times V_0^{0.71}$$

$$\max(\text{Si}_{\text{released}}) = 10^{1.54} \times \xi^{-2.92}$$
(6)

547 where V_0 is the initial volume (m³) and ξ is the reaction progress. 548 Combining these two relations allows predicting the reaction 549 progress corresponding to the maximal dissolution rate as a 550 function of the initial volume.

$$\xi_{\max(Si)} = 10^{-5.61} \times V_0^{-0.24} \tag{7}$$

Based on this equation, it is theoretically possible to estimate the time at which the release of Si is maximal when knowing the initial volume of an enstatite grain. Such empirical relations are very relevant for experimental works and practical applications because it corresponds to the attainment of the steady-state 556 regime of the dissolution (see Section 4.5). 557

4.1.3. Variability of Dissolution Rates for a Given Grain 558 Size. A long-standing concern in mineral/water interaction deals 559 with the uniqueness of the dissolution rate. 18,51 While the 560 variability of the dissolution rate is known to be significant when 561 the geochemical conditions are changed, it is often assumed, 562 particularly in reactive-transport studies, that the intrinsic 563 dissolution rate constant remains unchanged when the fluid 564 chemistry and the temperature are constant. However, several 565 studies tend to show that this assumption may be too simplistic, 566 as the dissolution rate may vary with time. While some studies 567 highlight a monotonic decrease of the dissolution rate with time 568 which can be associated with several factors such as the 569 development of amorphous silica-rich layers, 52 others emphasize 570 a complex evolution of the dissolution rate resulting from the 571 gradual modification of the crystal habit, 15,23,53 the inherited 572 history of the crystal reactivity 54,55 or the microstructural 573 differences (e.g., defect density) between two individual crystals 574 of a same mineral. 3,5,18,23,56-58 Therefore, it is central to 575 understand if two minerals placed under the same biogeochem- 576 ical conditions but differing in their history (one being fresh and 577 the other one being aged for example) will have the same 578 dissolution rate; hence, if two minerals of the same volume have 579 the same unique dissolution rate.

To investigate this question using the dissolution model, it has $\,$ 581 been decided to focus on the dissolution rate of the rectangular $\,$ 582 parallelepipeds when their volume reaches a volume equivalent $\,$ 583 to that of the smallest simulated crystal (14 \times 29 \times 250). The $\,$ 584 remaining volume is calculated with the number of atoms that $\,$ 585 are still in the rectangular parallelepiped at each iteration $\,$ 586 following $\,$ 587

$$V_{i} = \frac{a*b*c}{16} \left(N_{0} - \sum_{i}^{n=0} N_{n} \right)$$
(8) ₅₈

with V_i the volume at the ith iteration; a, b, and c the cell 589 parameters (m); N_0 the number of Si atoms in the enstatite 590 parallelepiped at the beginning of the simulation; and N_n , the 591 total number of Si released until the ith iteration. This mass 592 balance is divided by 16 since the enstatite cell is formed by 16 593 atoms of Si. The attainment of the volume corresponding to the 594 smallest crystal is indicated by the black circles in Figure 5, and 595 the dissolution rates at $V = V_{14 \times 29 \times 250}$ (named Si_{released, $V = V_{14 \times 29 \times 250}$) 596 as a function of the initial volume are shown in Figure 8c,d. 597 Interestingly, a relation between the initial volume and the 598 dissolution rates for $V = V_{14 \times 29 \times 250}$ exists}

$$Si_{\text{released, }V=V_{14\times29\times250}} = 10^{12.0} \times V_0^{0.44}$$
 (9) 600

This kind of relationships means that for a given volume, 601 different values of dissolution rates exist depending on the initial 602 size of the minerals.

4.2. Simple Mathematical Model of Si Dissolution 604 **Rate.** The evolution of Si dissolution rates and fluxes has a 605 specific behavior as described above. If this behavior seems 606 difficult to reproduce with a theoretical model, it is possible to 607 test hypotheses on how the dissolution evolves: here, we suggest 608 testing the assumption that the overall enstatite grain dissolution 609 simply corresponds to the sum of the contribution of the various 610 single faces delineating the enstatite volume. This assumption 611 may be true if, contrary to what is often proposed in the 612 literature, the edges and corners do not have a strong impact on 613

Kossel crystals

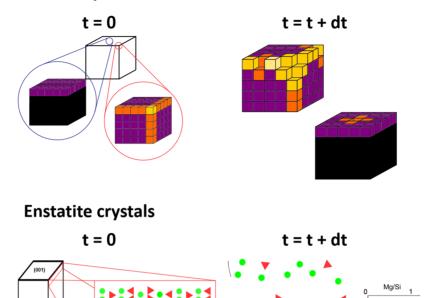


Figure 9. Scheme of the mechanism driving the dissolution of Kossel and enstatite crystals. Kossel: Black cubes represent atoms that are not at the mineral reactive surface. Purple, orange, and yellow cubes represent surface-, edge-, and corner-site atoms, respectively. During the dissolution, the atoms with fewer neighbors have a higher probability to be dissolved. This leads to the formation of rounded corners and edges. The atoms at the surface with only one neighbor missing (purple) are particularly difficult to dissolve compared to the others. Enstatite: at the beginning of the dissolution, Mg atoms are dissolved first. This is particularly visible on the (001) face where they exhibit a less populated first coordination sphere, leading to Mg depletion of the surface and the formation of a Si-enriched layer with a thickness not exceeding a few atomic layers. Because silica chains are not connected to each other, the probability of departure of Si atoms is the same on the entire (001) face, making it unlikely to exhibit rounded edges and corners.

614 the dissolution rate/flux and thus, if these sites do not lead to an 615 excessive rounding of the crystal. In this case, a simple cross-616 multiplication would be able to reproduce the evolution of the 617 dissolution rate/flux.

To model the dissolution of Si atoms, the first step is to consider the volume (ΔV_i) that is dissolved during an iteration

$$\Delta V_i = V_{i-1} - V_i \tag{10a}$$

$$V_i = (x_0 - 2\Delta h_i^{(100)})(y_0 - 2\Delta h_i^{(010)})(z_0 - 2\Delta h_i^{(001)})$$
(10b)

622 If the dissolved volume is known, the number of Si atoms 623 released per iteration can easily be calculated knowing the 624 volume of the enstatite cell and the number of Si atoms it 625 contains (16)

621

$$\operatorname{Si}_{\text{released},i} = \frac{16\Delta V_i}{abc} \tag{11}$$

Modeling the release rate of Si requires to know the values of 628 $\Delta h_i^{(hkl)}$ at each iteration step i, which requires to know the face-629 specific dissolution rate of enstatite both at steady state and 630 during the transient states, i.e., at the beginning and at the end of 631 the simulations. To the best of our knowledge, while an 632 analytical expression has been developed in Bouissonnié et al. 633 for the steady state, a similar expression does not exist for 634 transient phases. To model the dissolution of the rectangular 635 parallelepipeds used in the different simulations, we first

performed three additional face-specific simulations (i.e., 636 simulations where only the atoms belonging to the face (hkl) 637 are allowed to react, thus excluding atoms belonging to edges, 638 corners, and all other (h'k'l') faces), with a depth equivalent to 639 half the depth of the volume in a given direction. The evolution 640 of the surface retreats as a function of time for the (100), (010), 641 and (001) faces were then retrieved and implemented in eq 10b 642 to model the dissolution of a rectangular parallelepiped and 643 determine the evolution of the release rate of Si atoms as a 644 function of time. The results of this dissolution model are 645 presented in Figure 7 (light-colored curves) and compared to 646 the outputs of the simulations conducted with rectangular 647 parallelepipeds (dark-colored curves). The agreement between 648 both models is striking, with a sharp increase of the dissolution 649 rate observed during the first 8000 iterations, followed by a slow 650 decrease of the dissolution rate and a sharper decrease at the end 651 of simulations.

4.3. Comparison between Results of the Simulation 653 and Modeled Dissolution. Figure 7 shows that the results 654 derived from theoretical dissolution and modeled dissolution 655 are almost identical. With the exception of the very end of the 656 dissolution, the results of the simulations performed with 657 rectangular parallelepipeds and those derived from face-specific 658 dissolution are superimposed. However, contrary to the results 659 of the simulations performed with rectangular parallelepipeds, 660 those derived from face-specific dissolution exhibit a greater 661 standard variation around the mean value of the curves. This 662

f9f10

observation stems from the fact that stochastic variations in the instantaneous dissolution rate of each single face are cumulated, increasing the overall standard variation artificially. Interestingly, when one looks at the variation of the dissolution rate as a for function of the number of elapsed iterations (Figure 7a), the mean value of the results derived from the face-specific approach is slightly lower than the one derived from the simulations performed with rectangular parallelepipeds. This slight difference may be explained by the contribution of corners and edges to the dissolution rate/flux. However, contrary to other minerals, the dissolution of these surface sites seems to have a negligible impact. A scheme exhibiting the difference between enstatite and a Kossel crystal 19,19,36,37,59-61 dissolution, for which the contribution of edges and corners was shown in previous studies to be significant, is depicted in Figures 9 and 10 to

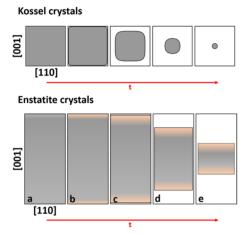


Figure 10. Scheme of the effect of dissolution through time on Kossel and enstatite crystals. Kossel: the high probability of departure of edge and corner sites leads to a rounding of the corresponding locations. This modifies significantly the crystal shape during the dissolution, which evolves from a cubic to a spherical shape. Black squares represent the crystal shape at t=0. The gray area represents a section of the crystal. Enstatite: At the beginning of the dissolution, Mg atoms are preferentially dissolved due to their particularly incomplete first coordination sphere, leading to the formation of a Si-enriched layer (orange area) on the (001) face (a-c). The Si-enriched layer reaches its constant depth (b,c) and the dissolution becomes stoichiometric. Both Si and Mg atoms are dissolved preferentially on the (001) face, but a few are dissolved on the (100) and (010) faces (c-e). This dissolution behavior makes the rounding of the crystals unlikely.

678 explain this counterintuitive result. These schemes are based on 679 the periodic bond chain theory, 17 which governs silicate 680 dissolution. In a Kossel crystal, the volume is composed of a 681 unique component ("atom"), leading to the existence of a single 682 type of bond. By nature, a Kossel crystal will have specific surface 683 sites (adatoms, steps, and kinks) with a high probability of departure, leading to the rounding of the simulated crystals over 685 time. In the case of enstatite, the anisotropic nature of pyroxenes 686 makes this morphological evolution simpler. As opposed to, e.g., tectosilicates, which have a three-dimensional framework of silica tetrahedrons, inosilicates are composed of silica chains 689 oriented following a specific direction (parallel to the c-axis in 690 enstatite). In enstatite, Mg and Si atoms are also organized in 691 planes parallel to the (100) face. This particular organization 692 explains the anisotropy of dissolution of enstatite, as discussed in 693 Bouissonnié et al., 16 and likely explains why macro steps and 694 corners do not play an essential role in the evolution of the

dissolution rate with time. Indeed, as shown in Figure 9, most of 695 enstatite dissolution flux is supported by (001) faces. This is due 696 to the fact that the release of Si from (*hk*0) faces requires the 697 simultaneous cleavage of two Si–O–Si bonds, while the release 698 of Si from (001) faces requires the cleavage of one Si–O–Si 699 bond only.

This specific anisotropic structure also explains why the 701 model depicted in Section 4.2 successfully matches the outputs 702 of the simulations run with enstatite parallelepipeds, indirectly 703 suggesting that no rounding of the crystals occurs with time. The 704 greater probability to release Mg atoms to the solution results in 705 the formation of a Mg-depleted zone at the mineral surfaces 706 during the first iterations (Figure 4), where the mineral- 707 solution interface is only composed of chains of Si atoms (Figure 708 9). This process is more pronounced at the surface of the (001) 709 faces, where Mg atoms have the greater departure probabilities. 710 This is fully consistent with the experimentally observed thicker 711 amorphous silica layers on (001) faces. If the (001) faces exhibit 712 a Mg-depleted mineral-solution interface, then it means that it 713 is composed essentially on silica chains, not connected between 714 them (Figure 9). These silica chains will be present throughout 715 the entire surface of the (001) face but, as their topmost Si atoms 716 all exhibit the same departure probability, a rounding of the 717 edges and kinks is unlikely to happen.

In summary, the dissolution of a Kossel crystal can be 719 described as follows: (i) Initial fast release of atoms from the 720 kinks and edges of the minerals; (ii) Through time, the Kossel 721 crystal habit evolves from a cubic to an almost spheroidal shape. 722 Conversely, the dissolution behavior of enstatite and more 723 generally, of pyroxenes, can be summarized as follows: (i) Rapid 724 depletion of the topmost Mg atoms from the (001) faces; (ii) 725 stabilization of the thickness of the corresponding silica layer; 726 and (iii) propagation of the dissolution front mainly from the 727 (001) faces. These mechanistic explanations are summarized in 728 Figures 9 and 10. Also, as mentioned in Section 2.4, the model is 729 not able to reproduce the amorphous silica layer. Then, the 730 interface mainly composed of Si atoms remains "crystalline" 731 with only disconnected silica chains. This may present a 732 limitation to the mechanisms developed above as, in natural 733 environment, a thicker amorphous silica layer may impact the 734 crystal shape evolution. Extending this discussion to other 735 minerals requires a specific treatment of other classes of 736 minerals, which is out of the scope of this study. However, it 737 is likely that many minerals, which highlight an anisotropy 738 similar to pyroxenes could observe a similar dissolution 739 mechanism. One could argue that many minerals are more 740 anisotropic than enstatite because of its orthorhombic Bravais 741 lattice, which has a high symmetry level. However, the notion of 742 anisotropy here refers to the organization of the Si tetrahedrons. 743 In this regard, orthorhombic inosilicates are less isotropic than, 744 e.g., triclinic tectosilicates, which have a three-dimensional 745 framework of silica tetrahedrons, even though the symmetry 746 level of the orthorhombic system is higher than that of the 747 triclinic system.

Finally, the main discrepancy between model's outputs and 749 theoretical results is observed at the end of the simulations. 750 While the dissolution rates calculated using the simulations run 751 with rectangular parallelepipeds reach 0 at the end of the 752 reaction, indicating that all of the material is consumed, it is not 753 the case for the rates calculated based on face-specific 754 dissolution rates and using eqs 10a and 10b. This observation 755 is an artifact resulting from the mathematical construction of the 756 model. While faces (100), (010), and (001) are considered, the 757

758 dissolution is mainly controlled by the sole (001) face. Equation 759 10b implies that all faces dissolve independently so that when 760 the length of the parallelepiped following the z-axis reaches 0, it 761 is not the case for the two other axes. Therefore, following eq 10b, a plan of enstatite contained in the two-dimensional (2D) 763 (xOy) plan still exists and continues to fuel the dissolution. 764 Conversely, in the real world (and in the simulations run with 765 rectangular parallelepipeds), the dissolution stops when the 766 crystal is completely dissolved.

4.4. Comparing Modeled Dissolution Fluxes and 767 768 Experimental Results. 4.4.1. Comparison Based on Dis-769 solution Experiments Conducted with Powdered vs Single-770 Face Enstatite. In the previous section, it has been shown that it is possible to reproduce the grain dissolution behavior with a simple mathematical model considering the dissolution fluxes of the faces in contact with the fluid. However, this good agreement was obtained using simulation results only. While, theoretically, the model used in the present study is also able to reproduce experimental data, ¹⁶ the corresponding validation has been previously based on a comparison with measured face-specific dissolution fluxes only, and not with results from powder 779 experiments. This missing comparison is therefore attempted hereafter. As a first step, we use below the additivity property of single-face dissolution fluxes illustrated in Section 4.3 to compare the results of dissolution experiments previously conducted with single faces with those conducted with powdered enstatite.

In their study, Oelkers and Schott¹¹ have determined the dissolution flux of enstatite powder over a wide range of pH and 787 temperature. Using the reaction order with respect to [H⁺] and the activation energy derived from their study, the dissolution flux of enstatite powder at 90 °C and pH 0 (the chemical conditions simulated in this study) should be around 2.35 × 791 10^{-8} mol/(m² s). In our previous study, the different dissolution 792 fluxes of the four main faces naturally exposed in enstatite have 793 been determined to yield 5.22×10^{-9} , 5.92×10^{-9} , 1.7×10^{-8} , 794 and 1.44×10^{-7} mol/(m² s) for the faces (100), (010), (210), 795 and (001) respectively (note that the results of Bouissonnié et 796 al. 16 were corrected by a 2-fold factor, as they considered 797 Mg₂Si₂O₆ as the chemical formula for enstatite, whereas Oelkers 798 and Schott used MgSiO₃). The main cleavage plan of enstatite is 799 $\{210\}^{62}$ and is likely to be the most abundant when enstatite is 800 crushed prior to run powder dissolution experiments. If one 801 assumes that, in enstatite powders, mostly (210) and (001) faces 802 are present, then based on the results of the previous section, the 803 dissolution flux of the powder can be calculated following:

$$r = \frac{4*S_{(210)}*r^{(210)} + 2*S_{(001)}*r^{(001)}}{S_0}$$
(12)

804

805 where $S_{(hkl)}$ is the surface area of the (hkl) face (m^2) , $r^{(hkl)}$ is the 806 dissolution flux $(\text{mol}/(\text{m}^2~\text{s}))$ of the (hkl) face, and S_0 is the 807 initial surface area (m^2) . Depending on the size of the grains 808 used in this calculation $(10\times 10\times 100~\text{or}~20\times 20\times 100~\mu\text{m}^3,$ 809 consistent with the grain size range reported in the Oelkers and 810 Schott study), the dissolution flux is estimated to be 2.85×10^{-8} 811 and $2.31\times 10^{-8}~\text{mol}/(\text{m}^2~\text{s})$ for $20\times 20\times 100$ and $10\times 10\times 10\times 100$ μm^3 crystals, respectively. These values are in excellent 813 agreement with the dissolutions flux calculated based on the 814 study of Oelkers and Schott (hereafter referred to as r_{OS}) $(2.35\times 10^{-8}~\text{mol}(\text{m}^2~\text{s}))$. This agreement further supports that edges 816 and corners must negligibly contribute to the dissolution flux of 817 enstatite grains, consistent with the previous section.

4.4.2. Testing Different Methods to Upscale Dissolution $_{819}$ Fluxes from Face-Specific Simulations to Powder Dissolution $_{820}$ Experiments. The ability of the model to reproduce dissolution $_{820}$ fluxes derived from powder experiments with dissolution fluxes $_{821}$ derived from face-specific simulations and experiments has been $_{822}$ shown in Sections 4.3 and 4.4.1, respectively. However, $_{823}$ simulating directly the dissolution of entire crystals with $_{824}$ dimensions of typical grains used in laboratory experiments $_{825}$ remains out of reach with current numerical methods. Indeed, $_{826}$ our computational capabilities allow us to simulate the $_{827}$ dissolution of crystals up to $_{829}$ typical enstatite grain size for powder dissolution experisely ments $_{829}$ ments $_{829}$ is on the order of $_{829}$ ments $_{829}$ ments $_{829}$ is on the order of $_{829}$ ments $_{829}$

To circumvent this problem, a solution is to consider the good 831 agreement between the results of the simulations run with 832 rectangular parallelepipeds and the results calculated using face-833 specific dissolution (eq 10a). As the surface retreat does not 834 depend on the considered surface area, each of the three main 835 phases of the dissolution of a given face (i.e., initial transient 836 regime, steady-state regime, i.e., linear increase of the surface 837 retreat with iterations, and terminal regime) extends over a 838 similar number of iterations, whatever the surface area 839 considered. We used this property to simulate the dissolution 840 of crystals with dimensions approaching those of grains used in 841 classical powder dissolution experiments (see Figure 11). This 842 ft1 process is repeated for all faces to simulate the dissolution of an 843 entire parallelepiped. The results of the simulations conducted 844 with this large volume are shown in Figures 5b and 6b (black 845) curves). This process allows studying the evolution of the 846 dissolution behavior over a wide range of volumes and also to 847 understand how such systems evolve. Ultimately, the simulation 848 of such large volumes allows comparing modeled and 849 experimental data.

The first important highlight is that no real steady state is 851 reached for dissolution rate/flux (Figures 5b and 6b). Indeed, 852 the dissolution rate and flux steadily increase over the course of 853 the simulation. This may be due to the evolution of the surface 854 area that is not correctly captured, as the calculation does not 855 consider its intrinsic variability over the entire surface (intrinsic 856 reactivity and etch pits formation for example). However, the $_{857}$ increase is slow and not significant (below 14 nmol/s, which 858 would remain out of reach of conventional techniques used to 859 measure dissolution fluxes in the laboratory), and this regime 860 can therefore be approximated to a steady state. This pseudo- 861 steady state corresponds to a mean dissolution flux of 862 approximately 1.8×10^{16} Si atoms/(m² iteration) which yields ₈₆₃ $2.62 \times 10^{-8} \text{ mol/(m}^2 \text{ s)}$, if one applies the time/iteration ₈₆₄ relationship calculated by Bouissonnié et al. $(r(mol/(m^2 s))) = 865$ $0.876 \times r(\text{mol/(m}^2 \text{ iteration)}))$. This value is in very good ₈₆₆ agreement with that determined by Oelkers and Schott (~1.11 867 r_{OS}).

Three additional upscaling methods are tested and compared $_{869}$ with r_{OS} .

The first method consists of considering the dissolution fluxes $_{871}$ determined with single-face dissolution experiments: 16 (a) with $_{872}$ faces (100), (010), and (001) and (b) with faces (210) and $_{873}$ (001)

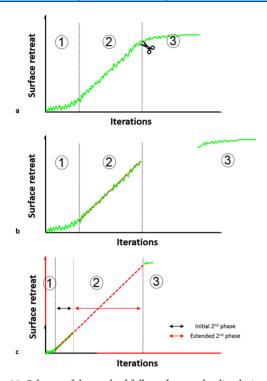


Figure 11. Scheme of the method followed to get the dissolution flux of enstatite rectangular parallelepipeds with a size comparable to those used in Oelkers and Schott. ¹¹ (a) Surface retreat simulated as a function of the iterations is used for each considered face (e.g., (100), (010), and (001)). It is divided into three different phases: (1) the transient regime, (2) the steady-state regime, and (3) the terminal regime, corresponding to the consumption of the remaining atoms in the materials. A cut is operated between the second and third phases. (b) A linear regression (dashed red line) is applied, based on the results of the steady-state phase starting from the transition between the first and second phases and ended between the second and third phases. (c) Linear regression is used to increase the size of the parallelepiped to reach the size used by Oelkers and Schott. The third phase is then added at the end of the extended second phase.

$$r = \frac{16*\Delta V(\Delta t)}{a*b*c*\Delta t*S_0*N_A}$$

$$\Delta V(\Delta t) = V_t - (x_t - 2\Delta h_{\Delta t}^{(100)|(210)})(y_t - 2\Delta h_{\Delta t}^{(010)|(210)})$$

$$(z_t - 2\Delta h_{\Delta t}^{(001)})$$

876 where r is the dissolution flux (mol/(m² s)), Δt is the time 877 interval considered for the calculation (s), S_0 is the initial surface 878 (m²), $N_{\rm A}$ is the Avogadro number (mol⁻¹), $\Delta V(\Delta t)$ is the

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879 difference of volumes over the time interval Δt (m³), and $\Delta h_{\Delta t}^{(hkl)}$ 880 is the surface retreat of the (hkl) face over the time interval Δt . 881 The second method uses the surrogate relation between the 882 dissolution flux and the probabilities (i.e., activation energies) 883 determined in Bouissonnié et al.⁴¹

 $\frac{\Delta h_{(hkl)}}{\Delta t} 0.876 \begin{bmatrix} k P_{\text{Mg}-\text{O}-\text{Mg}}^{\alpha} P_{\text{Mg}-\text{O}-\text{Si}}^{\beta} P_{\text{Si}-\text{O}-\text{Si}}^{\gamma} + \\ k_{\text{dis}} P_{\text{Mg}-\text{O}-\text{Mg}}^{\alpha_{\text{dis}}} P_{\text{Mg}-\text{O}-\text{Si}}^{\beta_{\text{dis}}} P_{\text{Si}-\text{O}-\text{Si}}^{\gamma_{\text{dis}}} (1 - e^{-\rho_{\text{d}}/\omega}) \end{bmatrix}$ (14)

885 with k, $k_{\rm dis}$, α , β , γ , $\alpha_{\rm dis}$, $\beta_{\rm dis}$, $\gamma_{\rm dis}$, and ω being empirical 886 parameters and $\rho_{\rm d}$ the dislocation density. The left-hand side of 887 the sum referred to the "bulk" dissolution flux, while the right-888 hand side referred to the contribution etch pits at dislocation

outcrops. The values of these parameters were determined in 889 Bouissonnié et al.⁴¹ and are listed in Table 1.

Table 1. Numerical Values of the Parameters in Equation 12 and Taken from Bouissonnié et al.⁴¹ a

C	(100)	(010)	(001)
face	(100)	(010)	(001)
k (Å/it)	8.87	7.8	4.72
α	2.46	2.22	6.36
β	4.62	4.65	4.19
γ	0.94	0.75	0.14
$k_{ m dis}$ (Å/it)	44.7	44.7*	
$lpha_{ m dis}$	2.09	2.09*	
$eta_{ m dis}$	4.09	4.09*	
$\gamma_{ m dis}$	0.67	0.67*	
ω	5.51×10^{10}	5.51×10^{10} *	
$\rho_{\rm d}(/{\rm cm}^2)$	4.9×10^{8}	9.8×10^{6}	0

 $^{\alpha}$ α, $^{\alpha}$ ρ, and $^{\gamma}$ represent fitting parameters for bulk dissolution rate (without the presence of dislocation). $^{\alpha}$ _{dis}, $^{\alpha}$ _{dis} and $^{\gamma}$ _{dis} represent fitting parameters for dissolution rate impacted by the presence of dislocations. The parameters k and k _{dis} represent the dissolution constant for bulk dissolution rate and dissolution rate impacted by the dislocation, respectively. $^{\omega}$ is a fitting parameter, and $^{\alpha}$ _d is the dislocation density measured in Bouissonnié et al. 16 (*) Parameters corresponding to the presence of dislocation on the (010) face were not studied. For this study, it has been assumed that they were equal to those of the (100) face.

The last method considers the modeled face-specific 891 dissolution fluxes given in Bouissonnié et al. 16 892

The three methods were applied on $20 \times 20 \times 100$ and 10×893 $10 \times 100~\mu\text{m}^3$ rectangular parallelepipeds (considered as a 894 model shape and size for the grains used in Oelkers and 895 Schott^{11,50}), and the results are summarized in Table 2. Overall, 896 t2 all methods exhibit a satisfactory agreement with the results 897 obtained experimentally, with discrepancies never exceeding 898 50%. Of note, a better agreement is obtained when the {210} 899 face is considered. This observation may confirm that enstatite 900 grains were mainly shaped with {210} face in the powder used 901

Table 2. Numerical Values of the Steady-State Dissolution Flux of an Enstatite Grain Considering the Simple Relation between Face-Specific Dissolution Flux and Powder Dissolution Flux Following Several Methods^a

method	crystal size (m³)	dissolution flux $(r = \text{mol}/(\text{m}^2 \text{ s})) (\times 10^{-8})$	r/r_{OS}
surface retreat of (100), (010), and (001) ¹⁶	$20 \times 20 \times 100 \mu\text{m}^3$	1.78	0.76
	$10 \times 10 \times 100 \; \mu\text{m}^3$	1.18	0.50
surface retreat of (210) and (001) ¹⁶	$20 \times 20 \times 100 \mu\text{m}^3$	2.75	1.17
	$10 \times 10 \times 100 \mu\text{m}^3$	2.17	0.92
surrogate	$20 \times 20 \times 100 \mu\text{m}^3$	2.22	0.94
model ⁴¹	$10 \times 10 \times 100 \mu\text{m}^3$	1.62	0.69
this study	$20 \times 20 \times 100 \mu\text{m}^3$	2.62	1.11
single-face- modeled results ¹⁶	$20 \times 20 \times 100 \mu\text{m}^3$	1.88	0.8
	$10 \times 10 \times 100 \mu\text{m}^3$	1.35	0.57

"The agreement (evaluated by the $r/r_{\rm OS}$ ratio) between powder dissolution experiments of Oelkers and Schott¹¹ and results obtained from face-specific dissolution experiments and modeling taken from Bouissonnié et al. ^{16,41} are reported in the last column. Crystal size has been chosen according to that reported in Oelkers and Schott, and an aspect ratio consistent with Dana. ⁵⁰

902 by Oelkers and Schott, which is consistent with the fact that 903 {210} represents the main cleavage plan of enstatite.

4.5. Relevance for Mineral Dissolution Studies and 905 Limitations. Both experimental results obtained with face-906 specific dissolution measurements and those obtained with the 907 stochastic dissolution model run with rectangular parallelepi-908 peds succeed to reproduce the dissolution rates/fluxes measured 909 during powder dissolution experiment. Here, we showed that 910 face-specific and powder dissolution rates can be linked using a 911 simple relation. However, this may be only true in the case of 912 very anisotropic minerals such as enstatite (and pyroxenes) 913 because edges and corners contribute negligibly to the 914 dissolution flux. This conclusion does not hold for calcite, for 915 example, as Noiriel et al.²⁵ showed that corners dissolve faster 916 than (104) cleavage plans. In our opinion, our results would 917 justify investigating the dissolution of other minerals according 918 to the methods reported here to determine the crystallographic 919 structures for which dissolution obeys relations similar to those 920 evidenced for enstatite.

The results presented here may also be useful to model silicate 922 weathering in natural environments. Subsurface environments 923 present a wide diversity of textures, from porous to fractured 924 media. Although fractured media should involve a preferential 925 water/solid interaction of a limited number of mineral cleavage 926 planes, porous media can exhibit a greater variety of mineral 927 faces in contact with water. Actually, as a first approximation, 928 micrometer-wide enstatite grains may be simplified as 929 rectangular parallelepipeds made of (210) and (001) faces 930 only, for which the length of the crystal in the z-direction is 5-10931 times greater than in the other directions leading to consider the 932 dissolution rate given by eq 12. This result may still hold true in 933 less acidic environment as long as the fluid is far from 934 equilibrium with respect to $SiO_{2(am)}$. The fact that face-935 specific and powder dissolution studies can be linked through a 936 simple relation for anisotropic minerals may imply that face-937 specific dissolution studies offer a greater interest than those 938 conducted with powders for minerals presenting an anisotropy 939 similar to the one of enstatite. In addition, our study shows the 940 prevalence of fast dissolving faces over the others, suggesting 941 that face-specific dissolution studies should target in priority 942 such faces. Overall, the agreement between the outputs of the 943 model and the theoretical results detailed in Section 4.2 shows 944 how important it is to consider the evolution of the reactive 945 surface area in geochemical/reactive-transport studies/models. 946 The evolution of the aspect ratio was shown to be important in 947 both cases when the reaction progress reaches approximately 948 80%. Indeed, at this step, the aspect ratio has evolved enough so 949 that the reaction flux is characterized by a sharp increase. This 950 may be of great interest to model chemical weathering in the regolith, where primary materials are altered into secondary 952 minerals and may be the main contributors of dissolved elements in springs and rivers.

Interestingly, the simulated instantaneous release rates of Mg stand Si atoms as a function of time (Figure 4) exhibit a specific shape that corresponds in every way to the calorimetry curves depicting the progress of cement hydration (cf. Figures 2–4 in standard to the calorimetry curves the dissolution of silicate minerals such as alite. It is noteworthy that such a shape has puzzled the materials sciences community for a couple of decades, since it reveals a strong nonlinearity of the dissolution rate with time, which is at odds with existing models of mineral reactivity. While previous attempts did not succeed to fully account for such observations, 65,66 the present

study suggests that the anisotropic dissolution of silicates may 965 indeed result in a general dissolution pattern consistent with 966 previous measurements of cement hydration, representing 967 relevant new avenues to be investigated in greater details. 968

Finally, among the main limitations of our study, the 969 development of amorphous silica-rich surface layers through 970 silica redeposition or surface network reorganization was not 971 considered, as the impact of such layers is suspected to be 972 nonsignificant in the experimental conditions investi- 973 gated 3,47,67,68 by Bouissonnié et al. 16 (i.e., very acidic pH and 974 low concentrations of aqueous silica). The implementation in 975 the stochastic dissolution code of backward reactions of Si 976 attachment, as described in, e.g., Zhang and Lüttge 69 or the 977 consideration of M–O hydrolysis instead of M–O–M 978 hydrolysis would be required to ultimately get closer to 979 conditions operating in natural settings.

5. CONCLUSIONS

In this work, we simulated the dissolution of enstatite grains with 981 a stochastic dissolution model developed at the atomic scale. By 982 varying the size of the simulated grains, we showed that the main 983 factor impacting the temporal evolution of the dissolution rate is 984 the aspect ratio. A similar evolution of the dissolution rate 985 through time is observed for grains with the same aspect ratio. 986 Furthermore, different parameters such as the maximum 987 dissolution rate, initial volume, dissolution at a given volume, 988 and reaction progress were linked together through empirical 989 functions.

One of the main outcomes of this study was provided by 991 comparing the outputs of the stochastic grain dissolution with a 992 theoretical dissolution model based on the sole contribution of 993 face-specific dissolution, neglecting the contribution of edges 994 and corners. The very good agreement between the two 995 methods highlights the modest effects of edges and corners 996 during enstatite dissolution, and probably, during the dis- 997 solution of other very anisotropic minerals as well (i.e., minerals 998 where the stronger atomic bonds are aligned in a specific 999 direction).

The comparison between modeled and experimental results 1001 obtained by Oelkers and Schott¹¹ on powder dissolution also 1002 revealed an excellent agreement. This led to the conclusion that 1003 powder dissolution results from the specific contribution of each 1004 face in a very simple way, making it possible to link the different 1005 experimental works performed in a laboratory.

Finally, this study shows the importance of fast dissolving 1007 faces. Indeed, almost the entire dissolution rate relies on the 1008 dissolution of the face (001). However, if the dissolution rates of 1009 the fastest dissolving faces are prominent, the overall dissolution 1010 rate is strongly correlated to the surface area of the other slower 1011 faces. This result supports the idea that reactive surface is one of 1012 the most important parameters in water/mineral interactions 1013 studies and that one must be aware, particularly in reactive-1014 transport studies, of what is the reactive surface and how it 1015 should be taken into account.

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